

Supplementary Materials

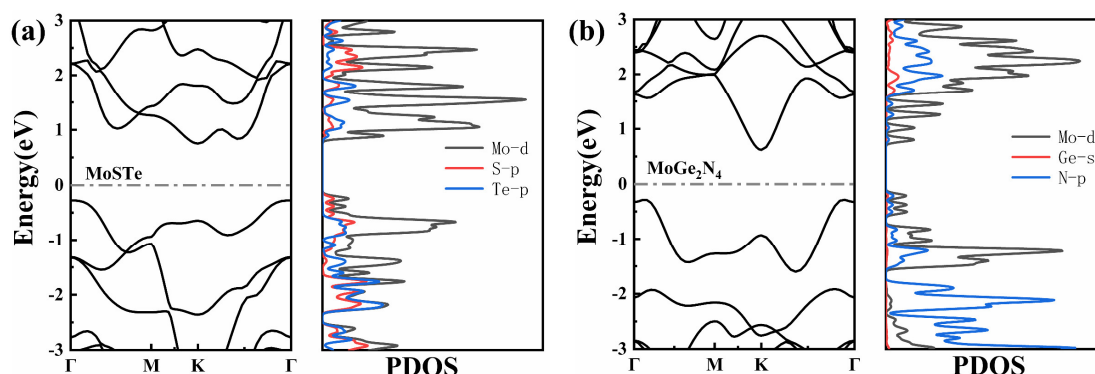
# Manipulable Electronic and Optical Properties of Two-Dimensional MoSTe/MoGe<sub>2</sub>N<sub>4</sub> van der Waals Heterostructures

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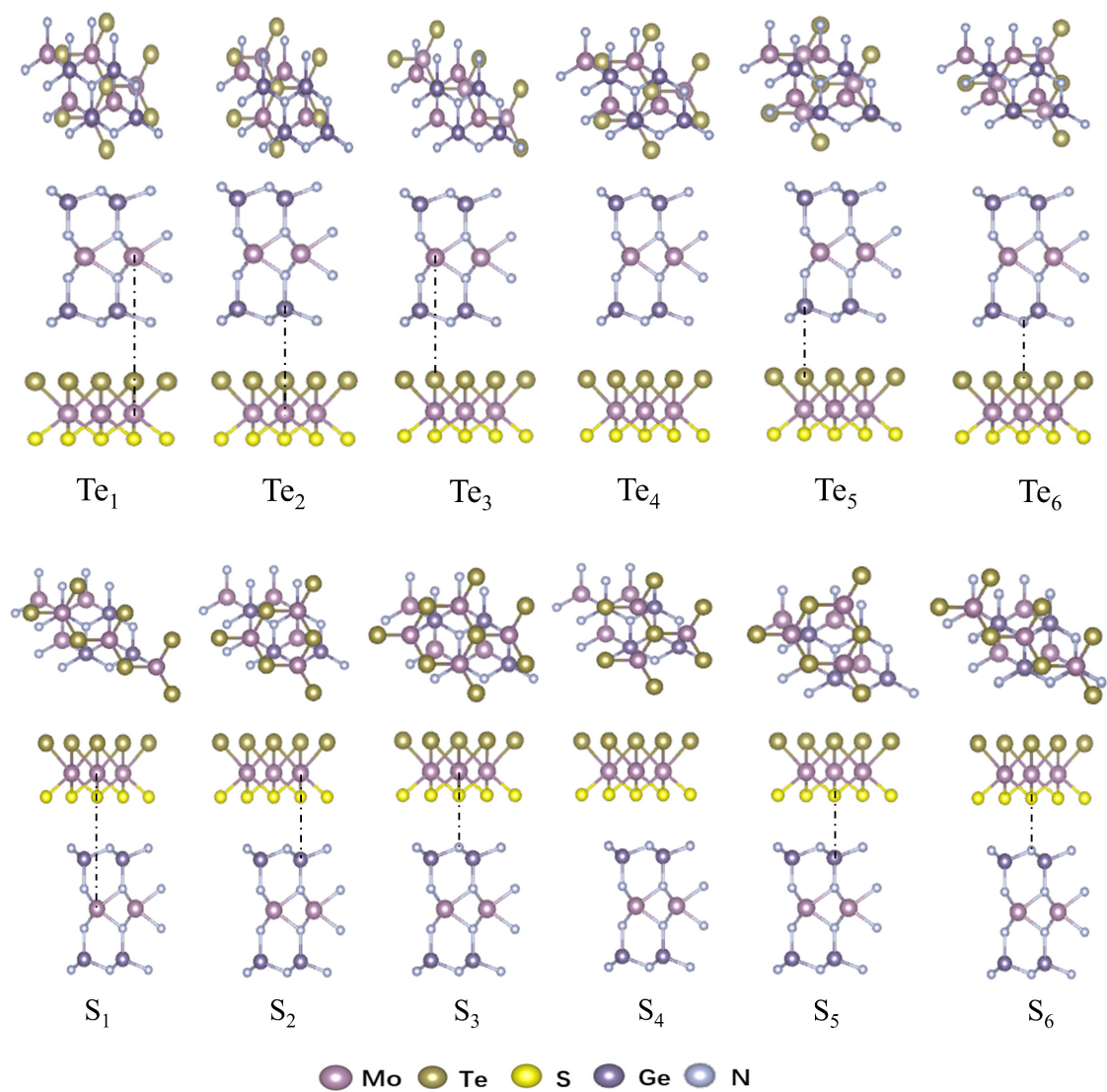
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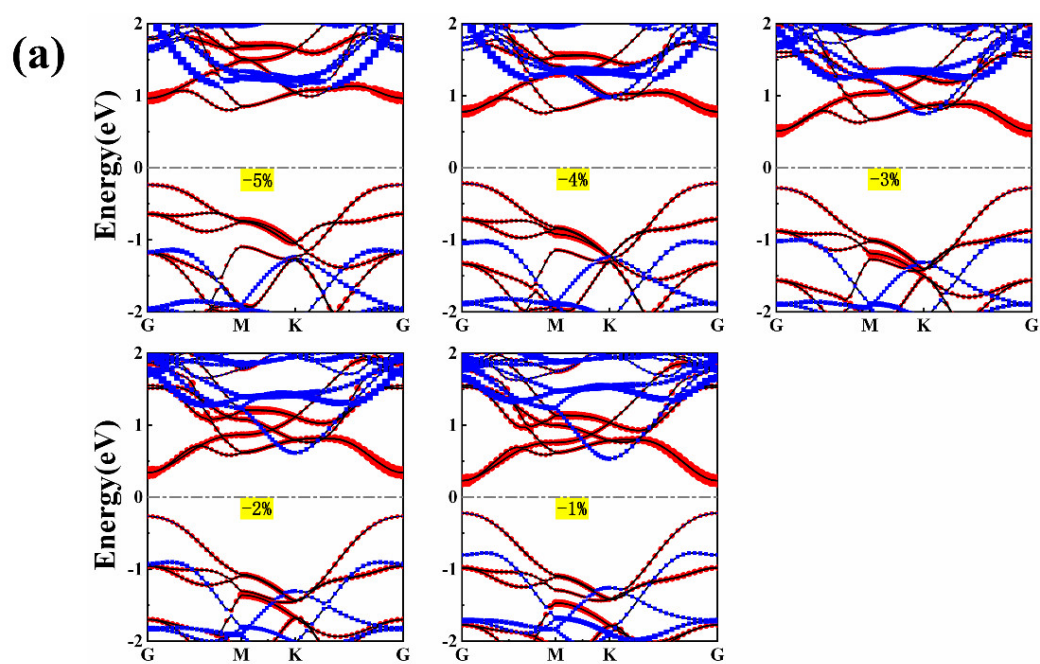
**Figure S1.** Band structures and PDOS of (a) Janus MoSTe monolayer and (b) MoGe<sub>2</sub>N<sub>4</sub> monolayer, respectively. The Fermi levels are set to zero.

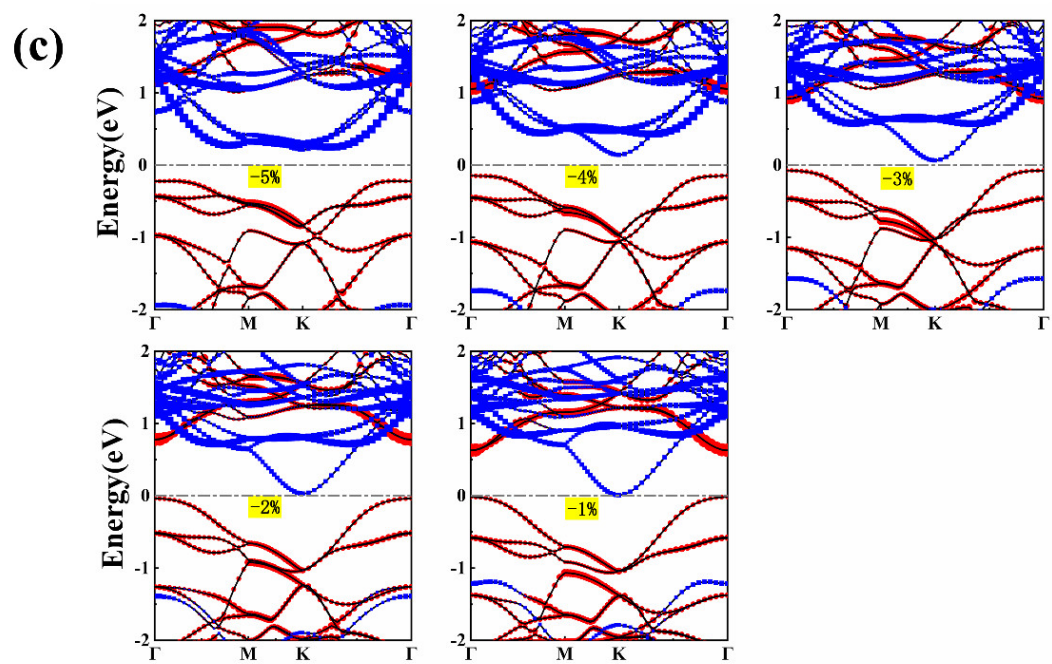
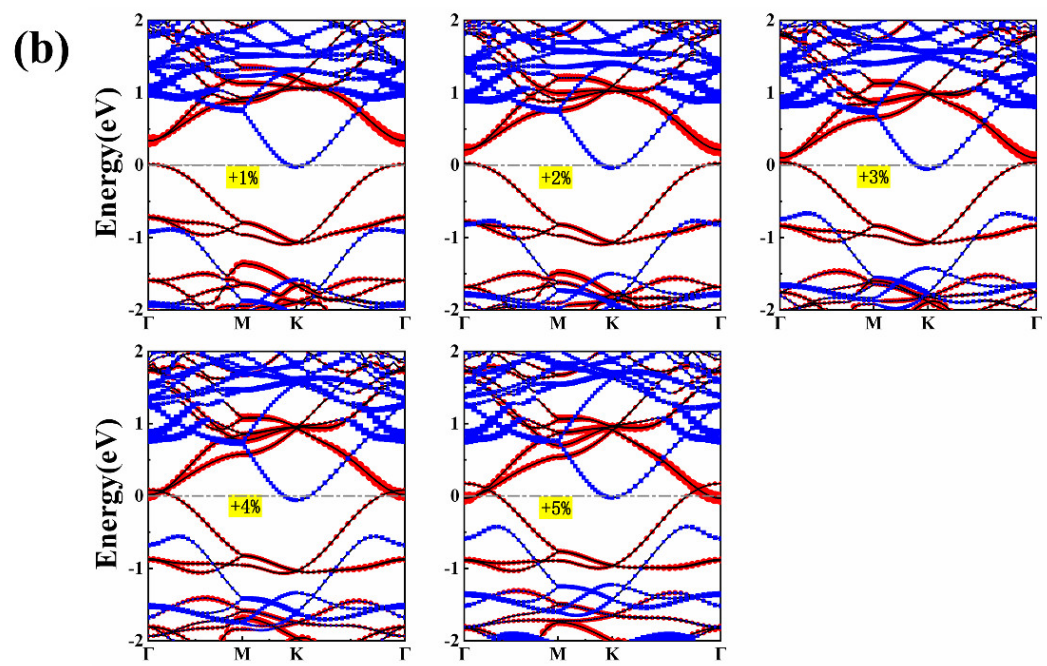
**Table S1.** : Binding energies ( $E_b$ ) of the optimized MoSTe/MoGe<sub>2</sub>N<sub>4</sub> vdWH for the twelve different stacking patterns.

Heterostructure	Te <sub>1</sub>	Te <sub>2</sub>	Te <sub>3</sub>	Te <sub>4</sub>	Te <sub>5</sub>	Te <sub>6</sub>
$E_b$ (meV)	-6.7680	-6.7679	-6.7671	-6.7710	-6.7670	-6.7708
Heterostructure	S <sub>1</sub>	S <sub>2</sub>	S <sub>3</sub>	S <sub>4</sub>	S <sub>5</sub>	S <sub>6</sub>
$E_b$ (meV)	-6.7396	-6.7407	-6.7405	-6.7434	-6.7427	-6.7394

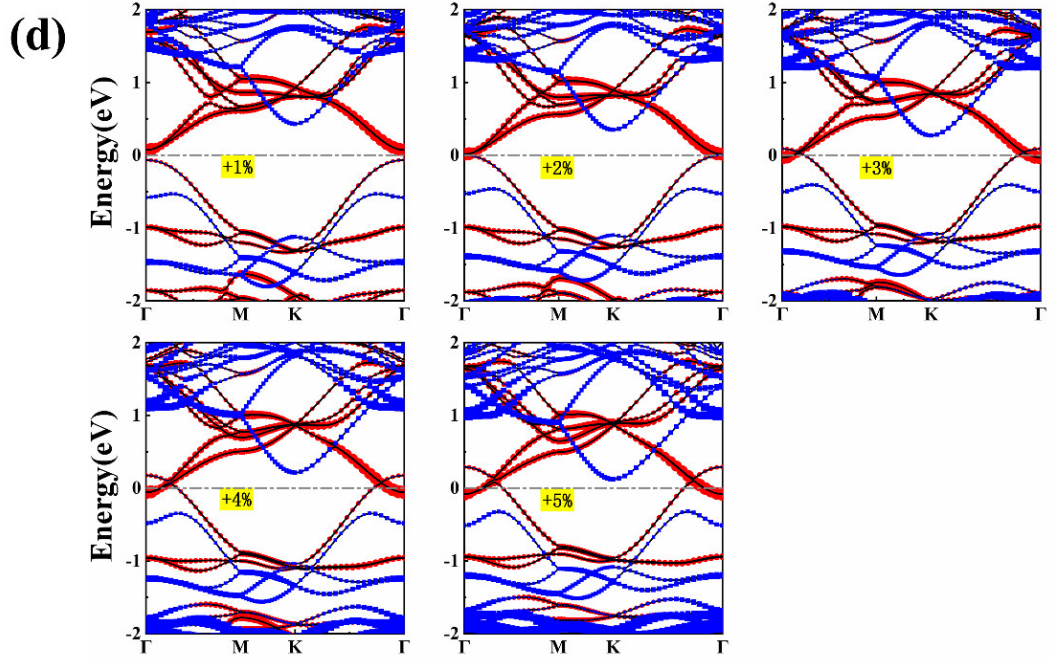


**Figure S2.** The optimized top and side views of the MoTe/MoGe<sub>2</sub>N<sub>4</sub> vdWH for twelve different stacking patterns.

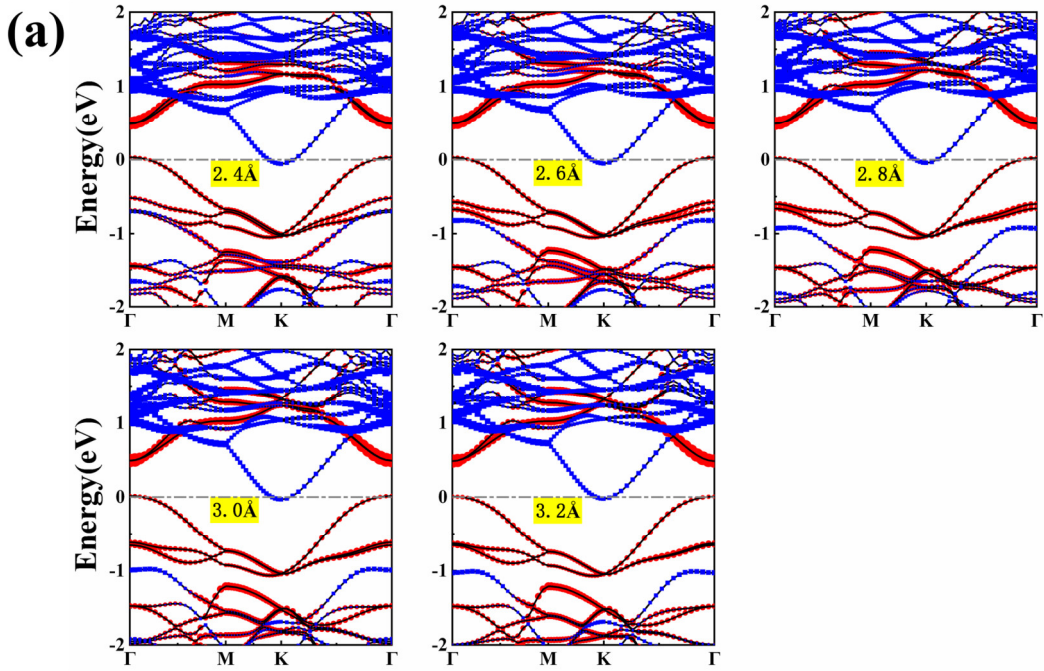


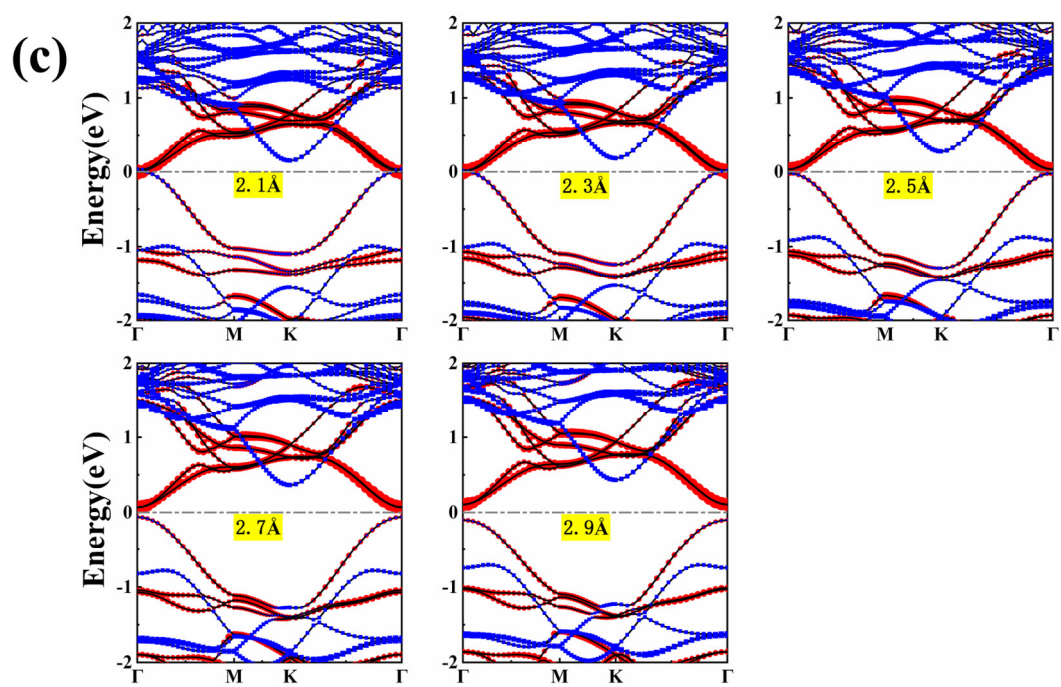
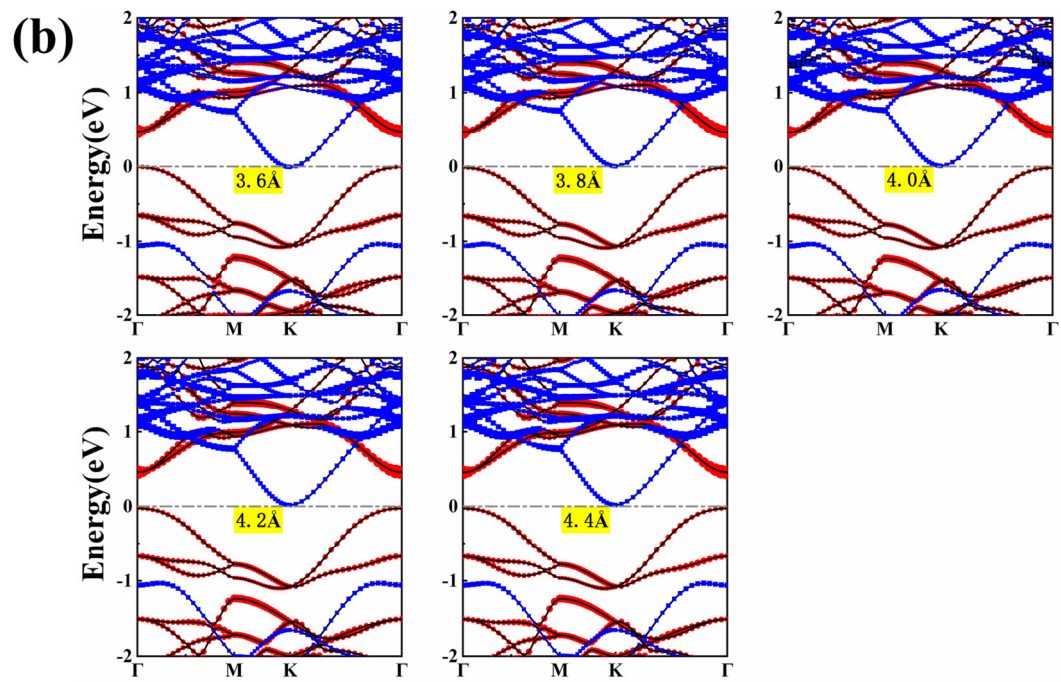


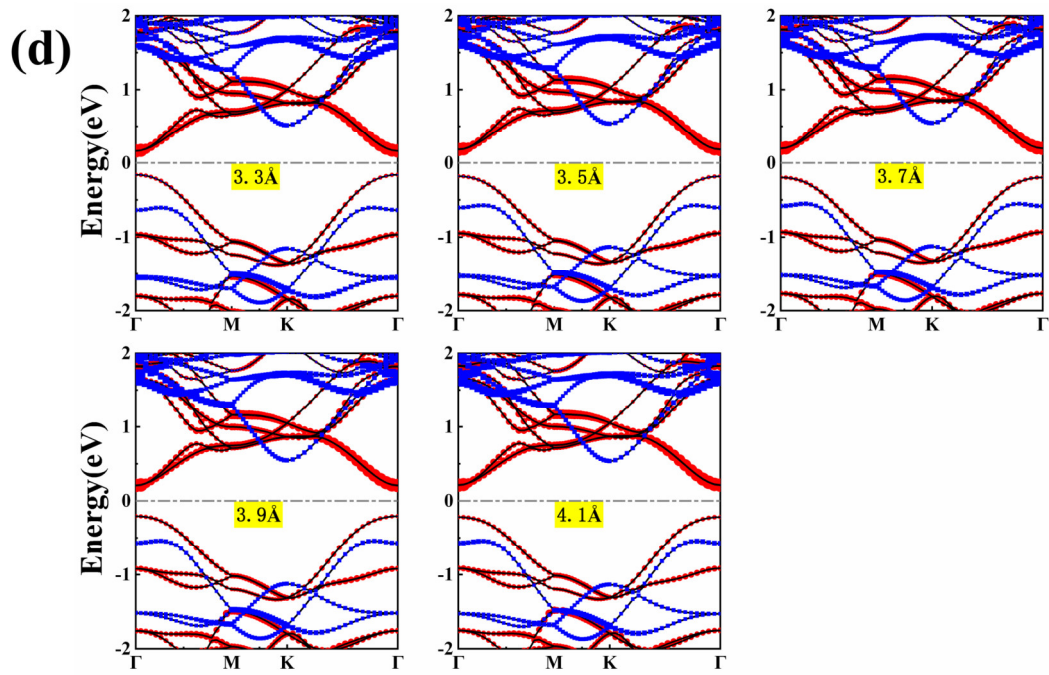




**Figure S3.** Band structures of (a) (b)  $\text{Te}_4\text{-MoSTe/MoGe}_2\text{N}_4$  vdWH, (c) (d)  $\text{S}_4\text{-MoSTe/MoGe}_2\text{N}_4$  vdWH under biaxial strains. The red and blue represent the weights from Janus MoSTe and  $\text{MoGe}_2\text{N}_4$  monolayers, respectively. Negative and positive values mean compressive stress and tensile stress.







**Figure S4.** Band structures of (a) (b)  $\text{Te}_4\text{-MoSTe/MoGe}_2\text{N}_4$  vdWH, (c) (d)  $\text{S}_4\text{-MoSTe/MoGe}_2\text{N}_4$  vdWH under different inter-layer distances, where the equilibrium interlayer distances are 3.4 Å and 3.1 Å, respectively. The red and blue represent the weights from Janus MoSTe and MoGe<sub>2</sub>N<sub>4</sub> monolayers, respectively. .